

General Purpose Transistor

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SC–89 package which is designed for low power surface mount applications.

Features

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

ORDERING INFORMATION

Device	Maring	Shippinṫg
LMBT2222ATT1G S-LMBT2222ATT1G	1P 1P	3000 / Tape & Reel
LMBT2222ATT3G S-LMBT2222ATT3G	1P 1P	10000 / Tape & Reel

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Rating	Symbol	Max	Unit
Collector–Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V _{CBO}	75	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	۱ _C	600	mAdc

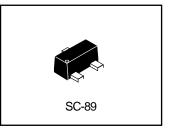
THERMAL CHARACTERISTICS

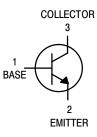
Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) T _A = 25°C	PD	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	833	°C/W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 1) ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	40	-	Vdc
Collector – Base Breakdown Voltage $(I_C = 10 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	75	-	Vdc
Emitter – Base Breakdown Voltage $(I_E = 10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)	I _{BL}	-	20	nAdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	-	100	nAdc







MARKING DIAGRAM



- 1P = Specific Device Code
 - = Date Code

Μ

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= Pb–Free Package



LMBT2222ATT1G;S-LMBT2222ATT1G

ON CHARACTERISTICS (Note 2)

Нсс			_
	35	-	
	50	-	
	75	-	
	100	-	
	40	-	
V _{CE(sat)}			Vdc
	-	0.3	
	-	1.0	
V _{BE(sat)}			Vdc
22(000)	0.6	1.2	
	-	2.0	
f _T	250	-	MHz
Cobo	-	8.0	pF
000			
Cibo	_	30	pF
100			
hie	0.25	1.25	kΩ
10			
hre	_	4.0	X 10 ⁻⁴
16		-	-
h _{fe}	75	375	-
16	-		
h _{oe}	25	200	μmhos
00			
NF	_	4.0	dB
	HFE VCE(sat) VBE(sat) fT Cobo Cibo hie hre hfe NF	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

SWITCHING CHARACTERISTICS

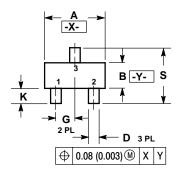
Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc},$	t _d	-	10	20
Rise Time	$I_{\rm C} = 150 \text{ mAdc}, I_{\rm B1} = 15 \text{ mAdc})$	t _r	-	25	ns
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 150 \text{ mAdc},$	t _s	-	225	ns
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$)	t _f	-	60	115

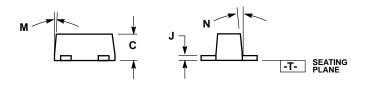
Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.
 Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.



LMBT2222ATT1G;S-LMBT2222ATT1G

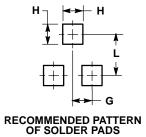
SC-89





- NOTES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETERS
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.60	1.70	0.059	0.063	0.067
В	0.75	0.85	0.95	0.030	0.034	0.040
С	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
Η	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004 0.006 0.		0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
Г	1.10 REF			0.043 REF		
М			10 °			10 °
N			10 °			10 °
s	1.50	1.60	1.70	0.059	0.063	0.067



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 NTE153MCP
 NTE16

 NTE195A
 NTE92
 C4460
 2N4401-A
 2N6728
 2SA1419T-TD-H
 2SA2126-E
 2SB1204S-TL-E
 2SC2712S-GR,LF
 2SC5488A-TL-H

 2SD2150T100R
 SP000011176
 2N2907A
 2N3904-NS
 2N5769
 2SC2412KT146S
 2SD1816S-TL-E
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 IMZ2AT108
 UMX21NTR
 MCH6102-TL-E

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